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High symbol rate transmissions with SiP modulators

Armands Ostrovskis^{1,2}, Krzysztof Szczerba³, Toms Salgals¹, Erik Norberg³, Michael Koenigsmann², John Sonkoly³, Kristaps Rubuls¹, Han Yun³, Benjamin Krüger², Molly Piels³, Arvids Sedulis¹, Fabio Pittalà², Sandis Spolitis¹, Markus Gruen², Hadrien Louchet², Robert Jahn², Kazuo Yamaguchi², Vjaceslavs Bobrovs¹, Xiaodan Pang^{4,5,1}, Robert Guzzon³, Oskars Ozoliņš^{1,5,4,*}

¹Institute of Photonics, Electronics and Telecommunications, Riga Technical University, 1048 Riga, Latvia

²Keysight Technologies Deutschland GmbH, 71034 Böblingen, Germany

³OpenLight Photonics, 6868 Cortona Dr., Goleta, CA 93117, USA

⁴Department of Applied Physics, KTH Royal Institute of Technology, 106 91 Stockholm, Sweden

⁵RISE Research Institutes of Sweden, 16440 Kista, Sweden

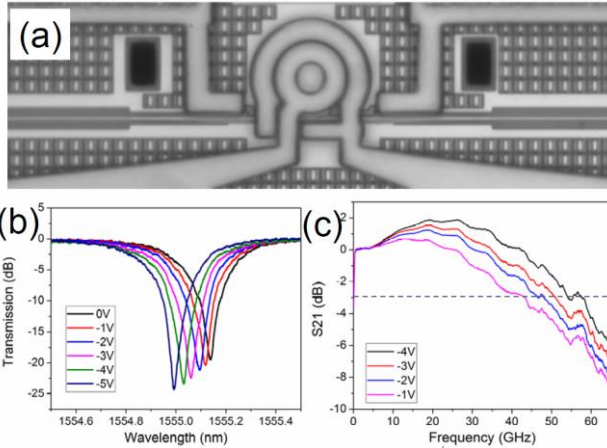
Outline

- State-of-the-art
- Key components
- Experimental setups
- Measurement results
- Conclusions

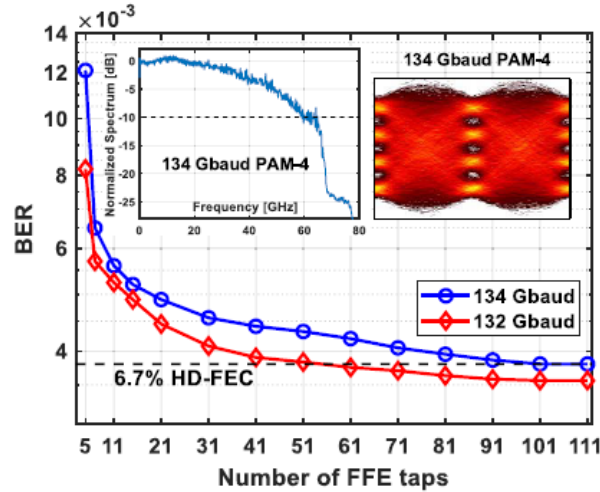
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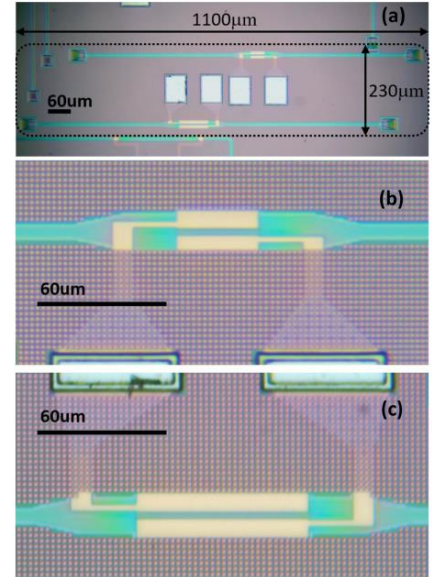
SOTA on SiP modulators



Tun-Yao Hung, et al., 300Gbit/s Si MRM,
OFC 2024, W4H.4



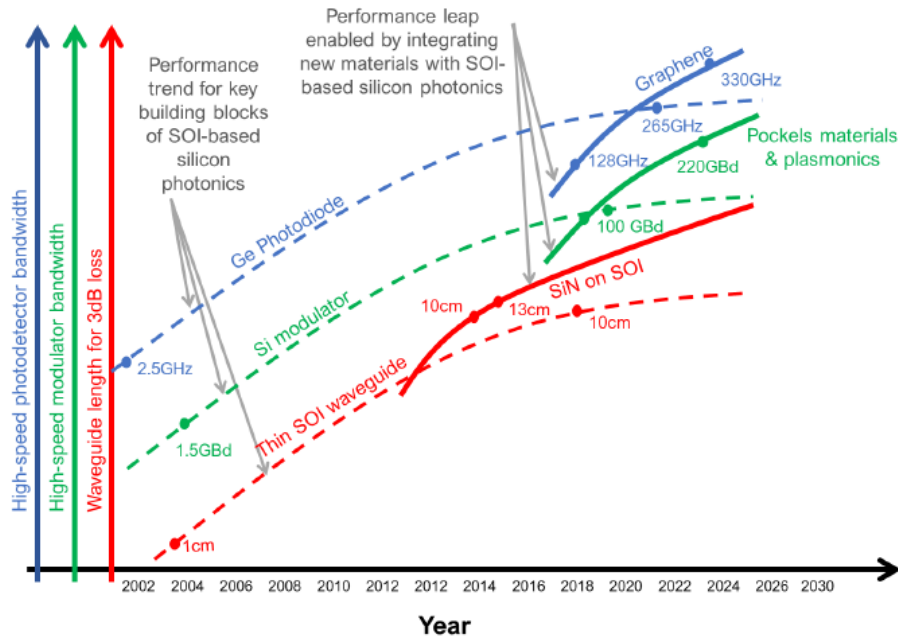
Md Samiul Alam, et al., 300Gbit/s Si MZM,
IEEE Photonics Technology Letters, 2021



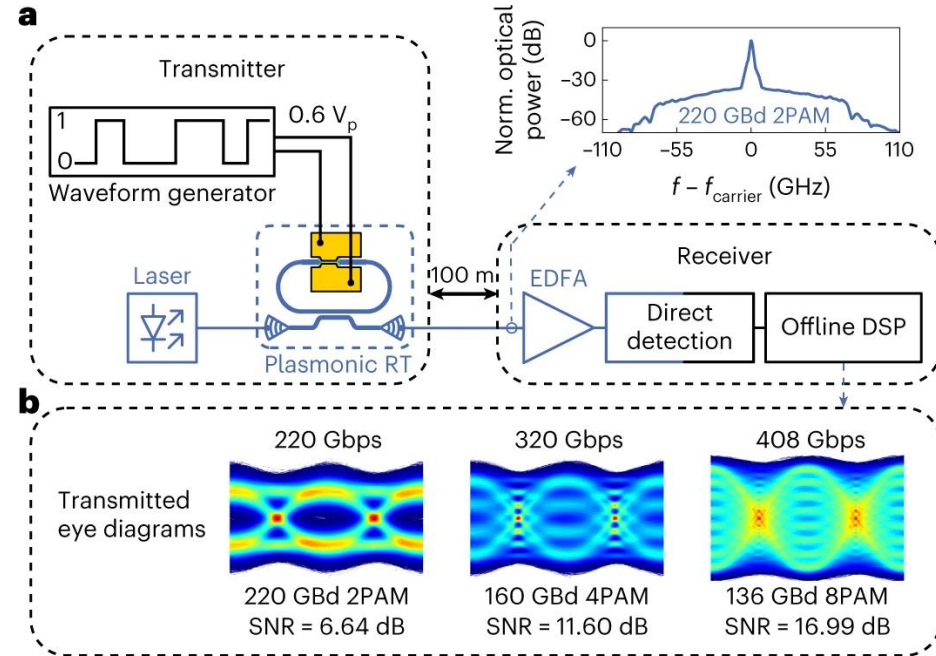
David W. U. Chan, et al., 224Gbit/s SiGe EAM,
Journal of Lightwave Technology, 2022

SOTA on heterogenous integration

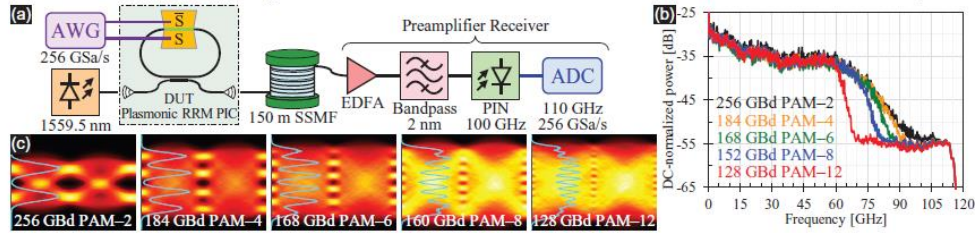
R. Baets, et al., Optical Materials Express, Dec. 2023



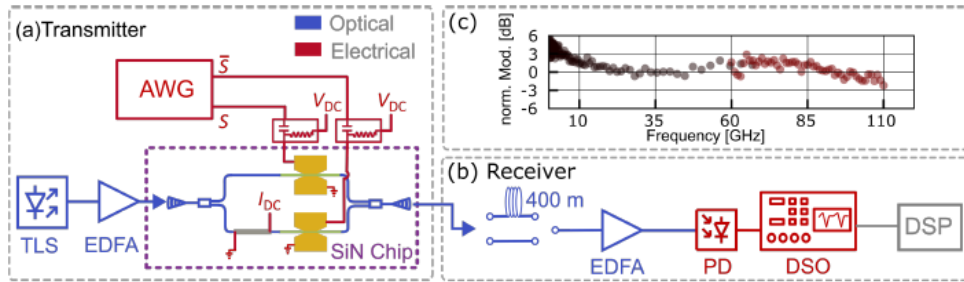
M. Eppenberger, et al., Nat. Photonics, 2023.



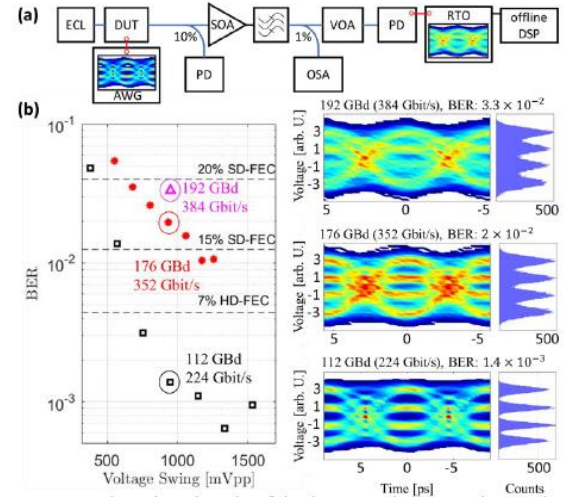
SOTA on heterogenous integration



Qian Hu, et al., 373 Gbit/s Plasmonics RRM, ECOC 2023, Th4B.6



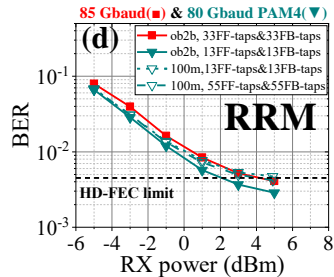
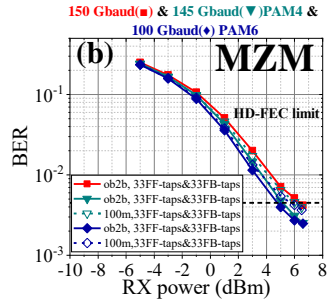
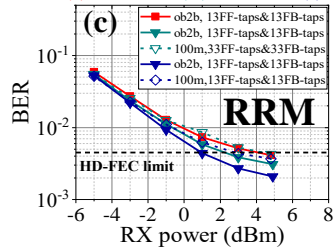
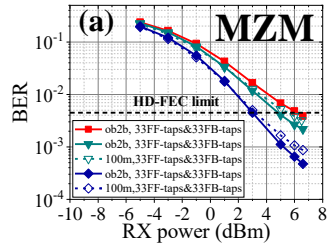
Manuel Kohli, et al., 340 Gbit/s BTO MZM, OFC 2024, M3K.5



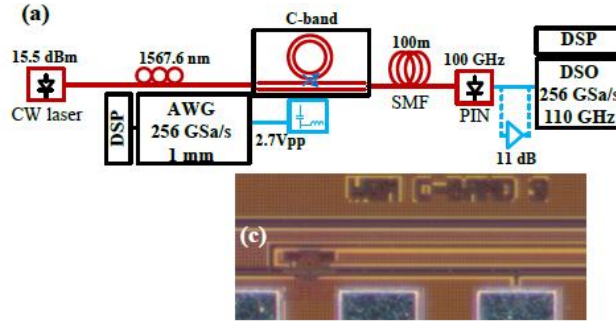
A. Schwarzenberger, et al., 384Gbit/s SOH MZM, OFC 2024, Th4B.6

Our contributions to SOTA

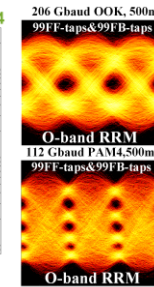
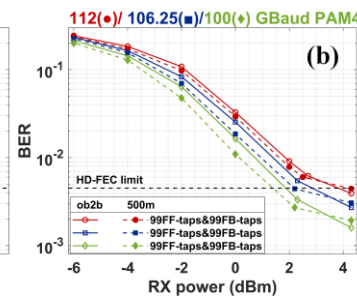
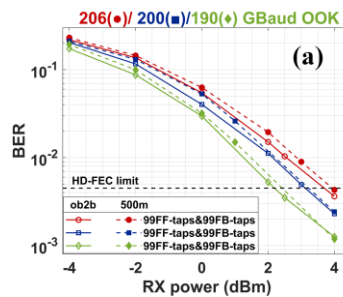
240 Gbaud(■) & 235 Gbaud(▼) & 220 Gbaud(●) OOK 160 Gbaud(■) & 155 Gbaud(▼) & 150 Gbaud(●) OOK



A.Ostrovskis, et al., 300/160 Gbit/s Si MZM/RRM, SiPhotonics 2023, PD.3



A.Ostrovskis, et al., 280 Gbit/s Si C-band RRM, Advanced Photonics Congress 2024



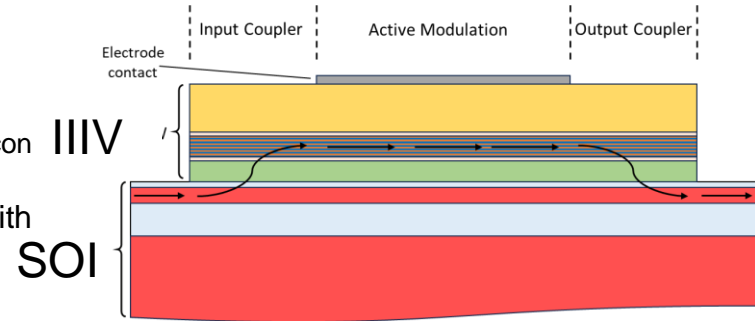
A.Ostrovskis, et al., 224 Gbit/s Si O-band RRM, CLEO-PR 2024

Outline

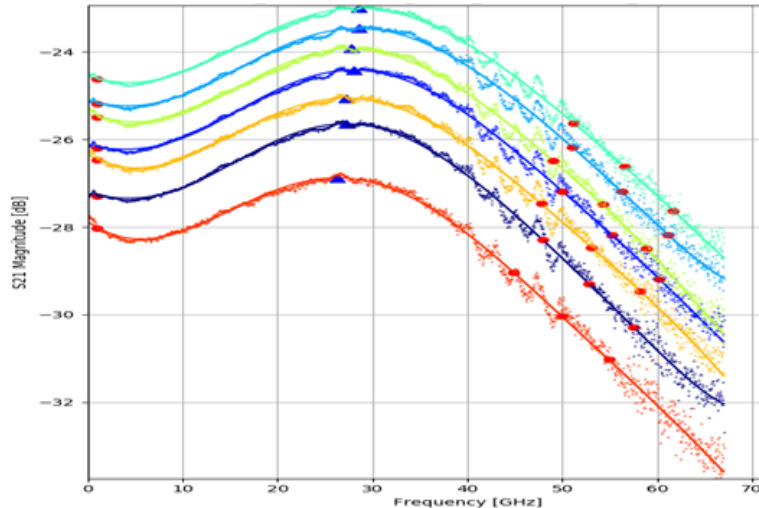
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Heterogenous III-V EAM on Silicon

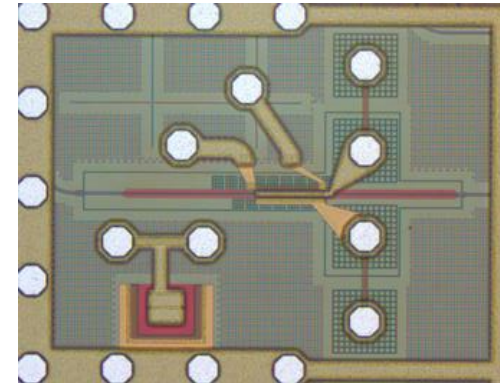
- III-V-EAM on Silicon fabricated at Tower Semiconductors
 - Design available in open market PDK
 - PDK/Process also includes integrated III-V lasers and full suite of silicon photonics components
- EAM designed for either single ended or differential drive, with on-PIC resistive and inductive termination
- EAM bandwidth >60GHz



Schematic cross-section of III-V on Si



Different bias values

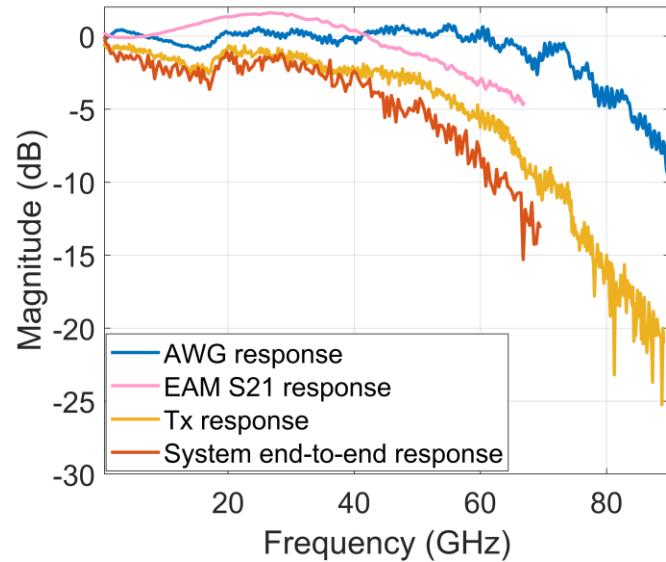
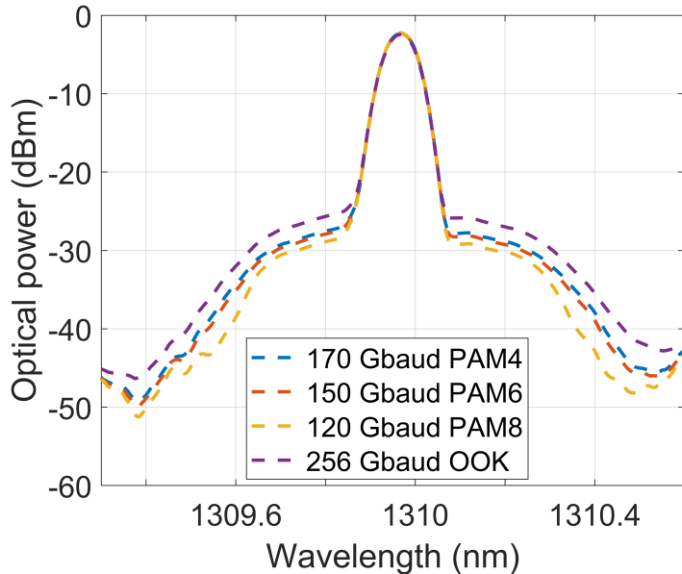
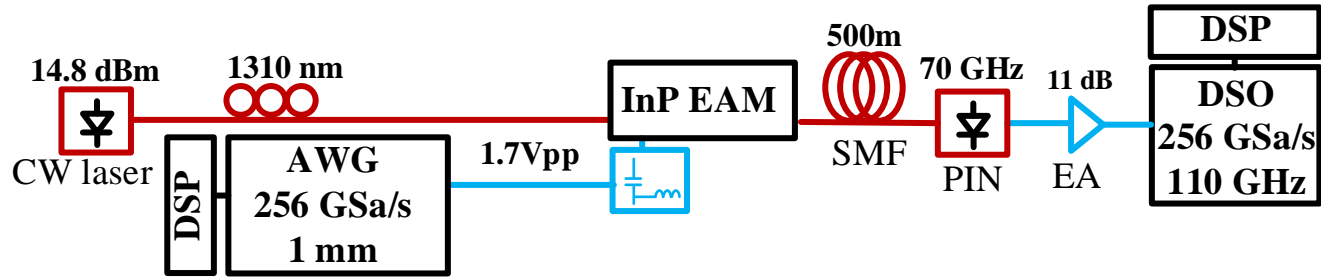


Optical image of fabricated EAM on Si

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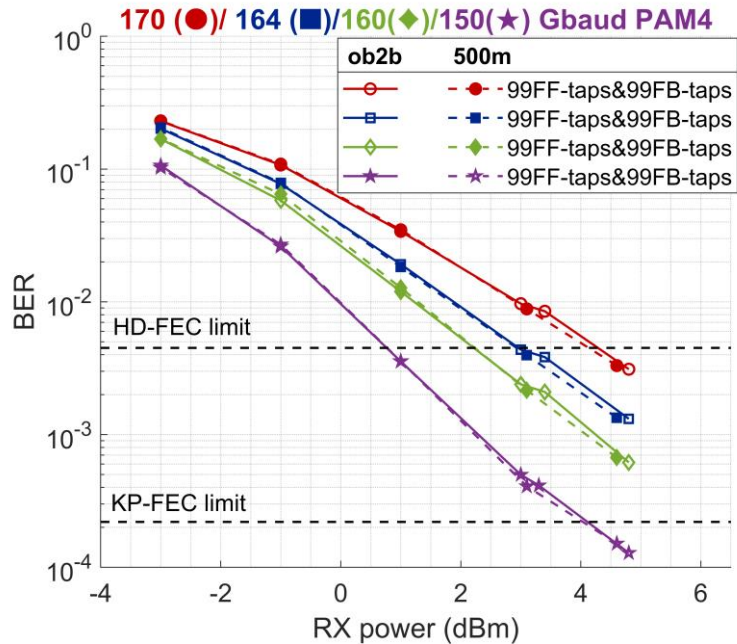
Experimental setup



Outline

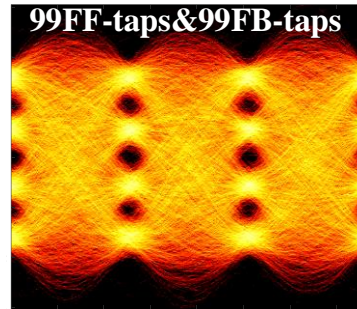
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BER curves and eye diagrams of PAM4

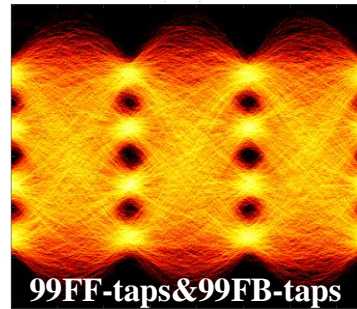
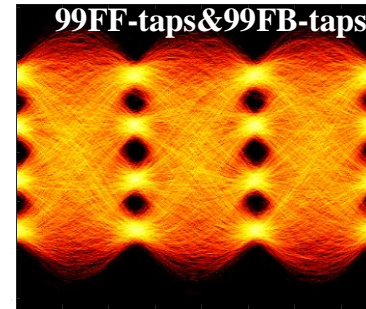


Post-equalization only with DFE

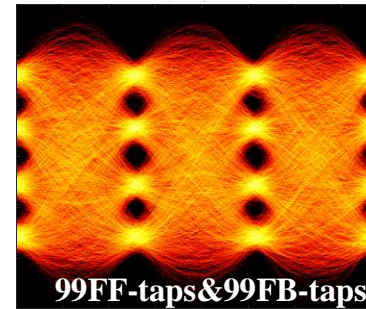
170 Gbaud PAM4, ob2b



150 Gbaud PAM4, ob2b

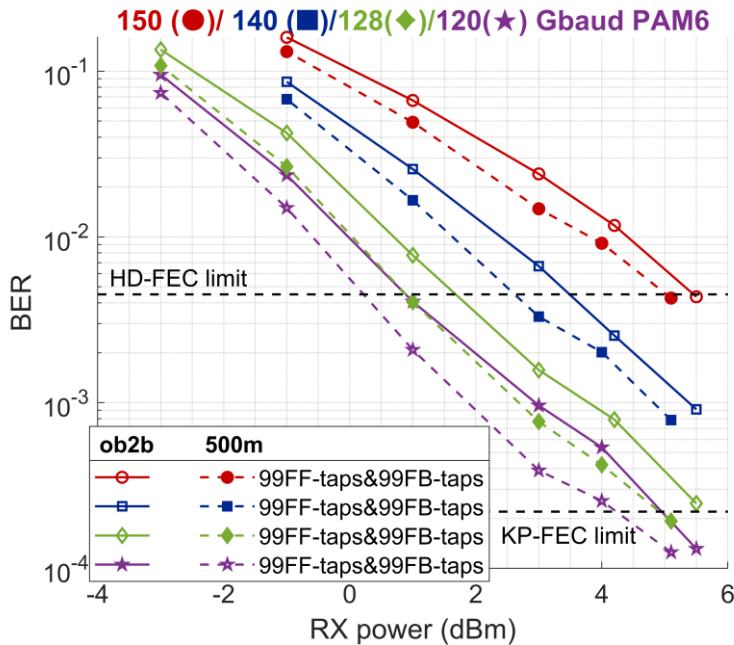


170 Gbaud PAM4, 500m



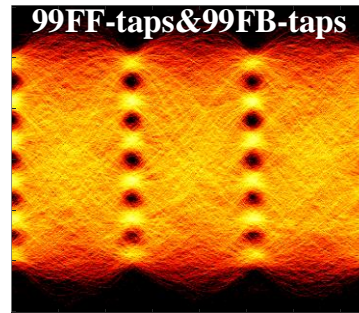
150 Gbaud PAM4, 500m

BER curves and eye diagrams of PAM6

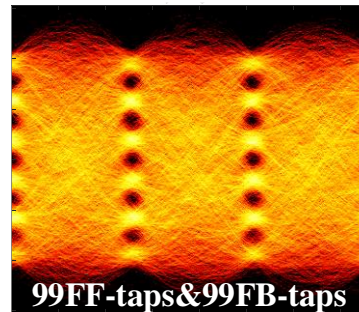
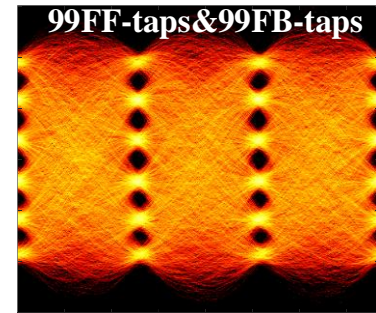


Post-equalization only with DFE

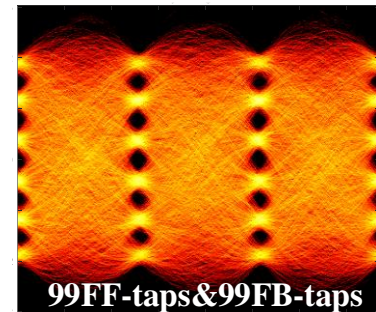
150 Gbaud PAM6, ob2b



120 Gbaud PAM6, ob2b

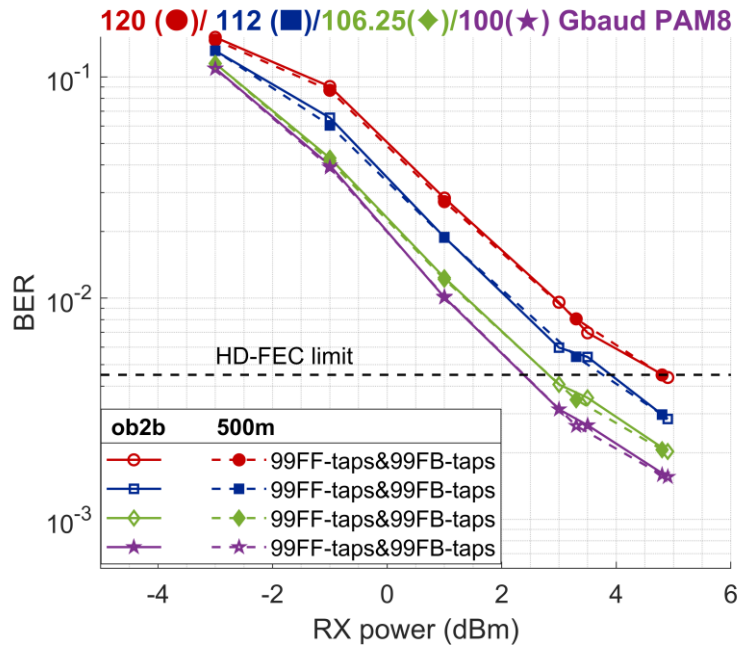


150 Gbaud PAM6, 500m

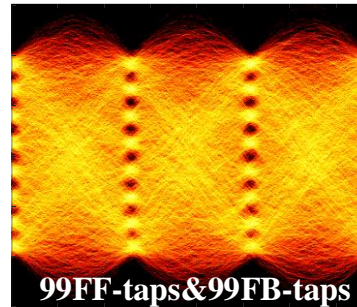
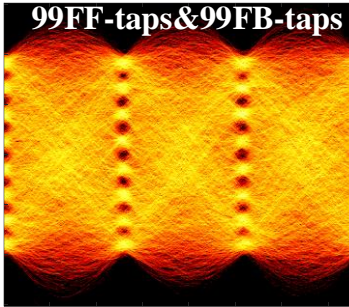


120 Gbaud PAM6, 500m

BER curves and eye diagrams of PAM8



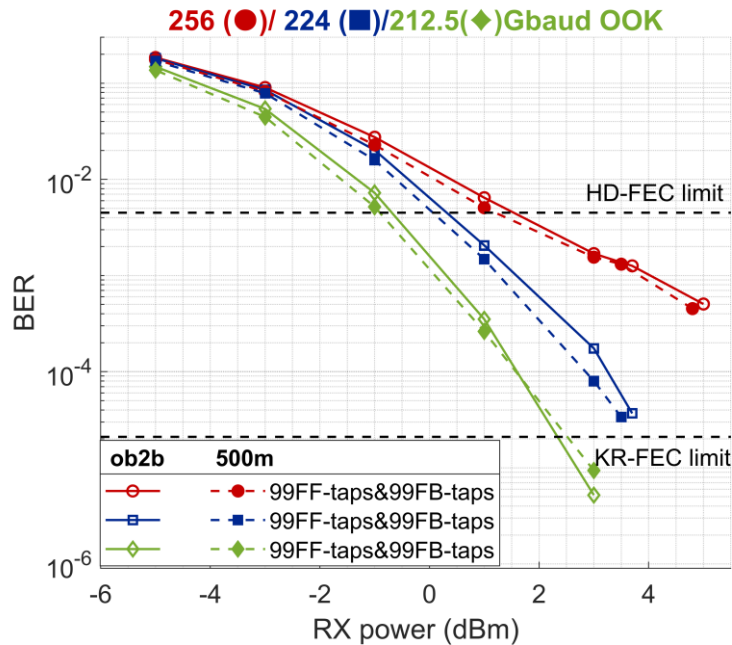
120 Gbaud PAM8, ob2b



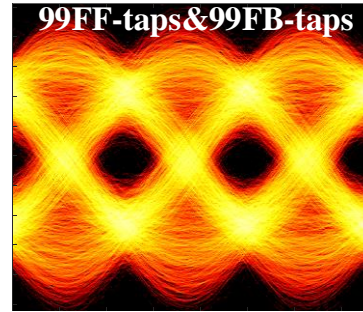
120 Gbaud PAM8, 500m

Post-equalization only with DFE

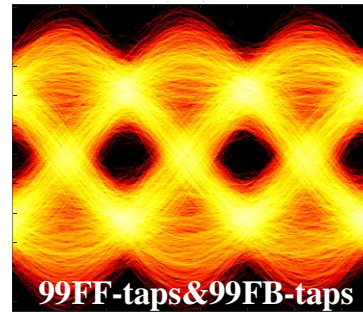
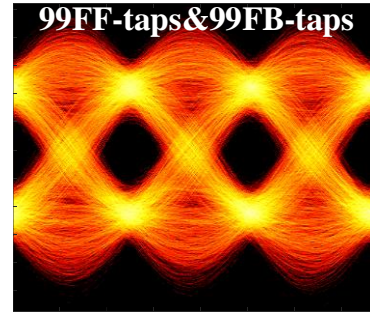
BER curves and eye diagrams of OOK



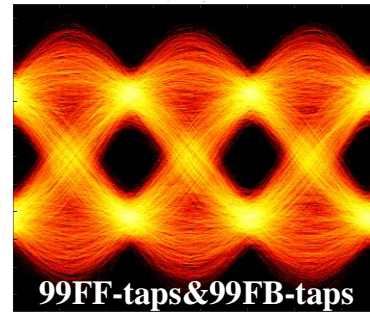
256 Gbaud OOK, ob2b



212.5 Gbaud OOK, ob2b



256 Gbaud OOK, 500m



212.5 Gbaud OOK, 500m

Post-equalization only with DFE

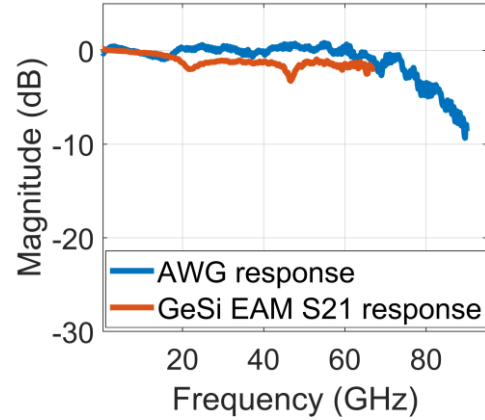
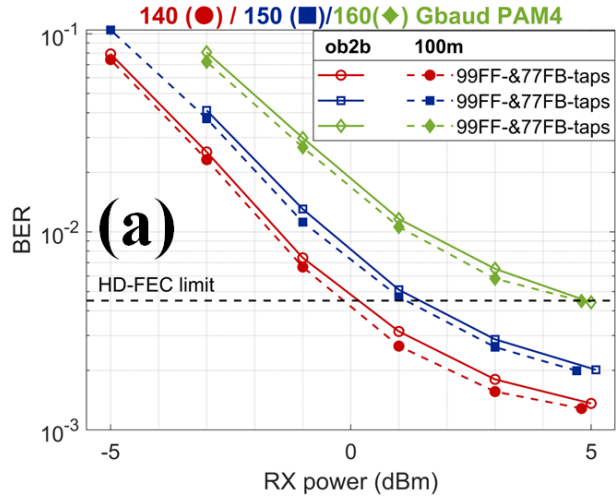
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Conclusions

- We demonstrate optical amplification-free O-band links with InP EAM with Si waveguides achieving up to 256 Gbaud OOK, 170 Gbaud PAM4 (**340 Gb/s**), 150 Gbaud PAM6 (**375 Gb/s**), and 120 Gbaud PAM8 (**360 Gb/s**) performance below the 6.25% overhead HD-FEC threshold after 500 m SMF transmission.
- We show 212.5 Gbaud OOK with performance satisfying KR-FEC requirements and 150 Gbaud PAM4 (**300 Gb/s**) as well as 120 Gbaud PAM6 (**300 Gb/s**) satisfying KP-FEC requirements.
- This paves the way for O-band DR and FR-compliant transceivers achieving a net bit rate beyond 200 Gbps/λ.

Advertisement break



Armands Ostrovskis, et al., Silicon Photonics GeSi Electro Absorption Modulator for Beyond 300 Gb/s Per λ Links, ECOC 2024, Tu1D: Intra-Data Center Systems **Tuesday 9:45, Harmonie 4**

Acknowledgement: EQUIPMENT



We thank **OpenLight Photonics** and **Tower Semiconductor** for the chips and components. The complete components list including on-chip lasers are available to the open market for the design of 200G/Lane heterogeneous silicon photonics PIC (DR and FR PIC) through **Tower Semiconductor PH18DA process design kit (PDK)**.

We also thank **Keysight Technologies** in Böblingen, Germany for hosting the experiment and for loaning the **N7776C-013 High Power Tunable Laser Source**, the **M8199B Arbitrary Waveform Generator** and the **UXR1104A Infiniium UXR-Series Oscilloscope**.



Acknowledgement: FUNDING

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- Swedish Research Council (VR) project 2019-05197 and 2022-04798
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Thank you for attention!

Armands Ostrovskis^{1,2}, Krzysztof Szczerba^{3, *}, Toms Salgals¹, Erik Norberg³, Michael Koenigsmann², John Sonkoly³, Kristaps Rubuls¹, Han Yun³, Benjamin Krüger², Molly Piels³, Arvids Sedulis¹, Fabio Pittalà², Sandis Spolitis¹, Markus Gruen², Hadrien Louchet², Robert Jahn², Kazuo Yamaguchi², Vjaceslavs Bobrovs¹, Xiaodan Pang^{4,5,1}, Robert Guzzon³, Oskars Ozoliņš^{1,5,4, *}

oskars.ozolins@rtu.lv

¹Institute of Photonics, Electronics and Telecommunications, Riga Technical University, 1048 Riga, Latvia

²Keysight Technologies Deutschland GmbH, 71034 Böblingen, Germany

³OpenLight Photonics, 6868 Cortona Dr., Goleta, CA 93117, USA

⁴Department of Applied Physics, KTH Royal Institute of Technology, 106 91 Stockholm, Sweden

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